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[International Rectifier \(Infineon Technologies Americas Corp.\)](#)
[IRG4PC60FPBF](#)

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sales@integrated-circuit.com

International **IR** Rectifier

INSULATED GATE BIPOLAR TRANSISTOR

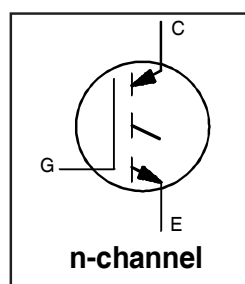
PD - 95566A

IRG4PC60FPbF

Fast Speed IGBT

Features

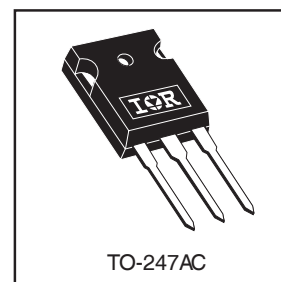
- Fast: Optimized for medium operating frequencies (1-5 kHz in hard switching, >20 kHz in resonant mode).
- Generation 4 IGBT design provides tighter parameter distribution and higher efficiency.
- Industry standard TO-247AC package.
- Lead-Free



$V_{CES} = 600V$
$V_{CE(on) typ.} = 1.50V$
@ $V_{GE} = 15V, I_C = 60A$

Benefits

- Generation 4 IGBT's offer highest efficiency available
- IGBT's optimized for specified application conditions
- Designed for best performance when used with IR Hexfred & IR Fred companion diodes.



Absolute Maximum Ratings

	Parameter	Max.	Units
V_{CES}	Collector-to-Emitter Breakdown Voltage	600	V
$I_C @ T_C = 25^\circ C$	Continuous Collector Current	90	A
$I_C @ T_C = 100^\circ C$	Continuous Collector Current	60	
I_{CM}	Pulsed Collector Current ①	360	
I_{LM}	Clamped Inductive Load Current ②	360	
V_{GE}	Gate-to-Emitter Voltage	± 20	V
E_{ARV}	Reverse Voltage Avalanche Energy ③	200	mJ
$P_D @ T_C = 25^\circ C$	Maximum Power Dissipation	520	W
$P_D @ T_C = 100^\circ C$	Maximum Power Dissipation	210	
T_J	Operating Junction and	-55 to + 150	$^\circ C$
T_{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 seconds	300 (0.063 in. (1.6mm from case)	
	Mounting torque, 6-32 or M3 screw.	10 lbf•in (1.1N•m)	

Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	0.24	$^\circ C/W$
$R_{\theta CS}$	Case-to-Sink, Flat, Greased Surface	0.24	—	
$R_{\theta JA}$	Junction-to-Ambient, typical socket mount	—	40	
Wt	Weight	6 (0.21)	—	g (oz)

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Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)CES}$	Collector-to-Emitter Breakdown Voltage	600	—	—	V	$V_{GE} = 0V, I_C = 250\mu A$
$V_{(BR)ECS}$	Emitter-to-Collector Breakdown Voltage ④	16	—	—	V	$V_{GE} = 0V, I_C = 1.0A$
$\Delta V_{(BR)CES}/\Delta T_J$	Temperature Coeff. of Breakdown Voltage	—	0.13	—	V/°C	$V_{GE} = 0V, I_C = 1.0mA$
$V_{CE(ON)}$	Collector-to-Emitter Saturation Voltage	—	1.5	1.8	V	$I_C = 60A, V_{GE} = 15V$
		—	1.7	—		$I_C = 90A$
		—	1.5	—		$I_C = 60A, T_J = 150^\circ\text{C}$
$V_{GE(th)}$	Gate Threshold Voltage	3.0	—	6.0		$V_{CE} = V_{GE}, I_C = 250\mu A$
$\Delta V_{GE(th)}/\Delta T_J$	Temperature Coeff. of Threshold Voltage	—	-11	—	mV/°C	$V_{CE} = V_{GE}, I_C = 250\mu A$
g_{fe}	Forward Transconductance ⑤	36	69	—	S	$V_{CE} = 100V, I_C = 60A$
I_{CES}	Zero Gate Voltage Collector Current	—	—	250	μA	$V_{GE} = 0V, V_{CE} = 600V$
		—	—	2.0		$V_{GE} = 0V, V_{CE} = 10V, T_J = 25^\circ\text{C}$
		—	—	1000		$V_{GE} = 0V, V_{CE} = 600V, T_J = 150^\circ\text{C}$
I_{GES}	Gate-to-Emitter Leakage Current	—	—	± 100	nA	$V_{GE} = \pm 20V$

Switching Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
Q_g	Total Gate Charge (turn-on)	—	290	340	nC	$I_C = 40A$
Q_{ge}	Gate - Emitter Charge (turn-on)	—	40	47		$V_{CC} = 400V$
Q_{gc}	Gate - Collector Charge (turn-on)	—	100	130		$V_{GE} = 15V$
$t_{d(on)}$	Turn-On Delay Time	—	42	—	ns	$T_J = 25^{\circ}C$
t_r	Rise Time	—	66	—		$I_C = 60A, V_{CC} = 480V$
$t_{d(off)}$	Turn-Off Delay Time	—	310	360		$V_{GE} = 15V, R_G = 5.0\Omega$
t_f	Fall Time	—	170	220	mJ	$V_{GE} = 15V, R_G = 5.0\Omega$
E_{on}	Turn-On Switching Loss	—	0.30	—		Energy losses include "tail"
E_{off}	Turn-Off Switching Loss	—	4.6	—		See Fig. 10, 11, 13, 14
E_s	Total Switching Loss	—	4.9	6.3	ns	$T_J = 150^{\circ}C,$ $I_C = 60A, V_{CC} = 480V$ $V_{GE} = 15V, R_G = 5.0\Omega$ Energy losses include "tail"
$t_{d(on)}$	Turn-On Delay Time	—	39	—		
t_r	Rise Time	—	66	—		
$t_{d(off)}$	Turn-Off Delay Time	—	470	—	mJ	See Fig. 13, 14
t_f	Fall Time	—	300	—		
E_s	Total Switching Loss	—	8.8	—		
L_E	Internal Emitter Inductance	—	13	—	nH	Measured 5mm from package
C_{ies}	Input Capacitance	—	6050	—	pF	$V_{GE} = 0V$
C_{oes}	Output Capacitance	—	360	—		$V_{CC} = 30V$
C_{res}	Reverse Transfer Capacitance	—	66	—		$f = 1.0MHz$

Notes:

- ① Repetitive rating; $V_{GE} = 20V$, pulse width limited by max. junction temperature. (See fig. 13b)
- ② $V_{CC} = 80\%(V_{CES})$, $V_{GE} = 20V$, $L = TBD \mu H$, $R_G = 5.0\Omega$. (See fig. 13a)
- ③ Repetitive rating; pulse width limited by maximum junction temperature.
- ④ Pulse width $\leq 80\mu s$; duty factor $\leq 0.1\%$.
- ⑤ Pulse width $5.0\mu s$, single shot.

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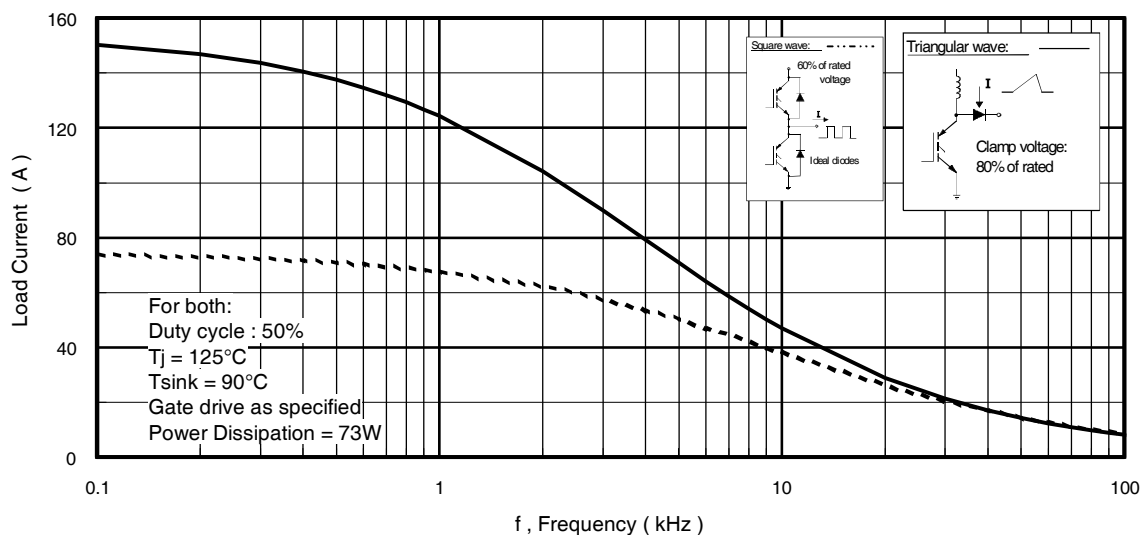


Fig. 1 - Typical Load Current vs. Frequency
(For square wave, $I = I_{RMS}$ of fundamental; for triangular wave, $I = I_{PK}$)

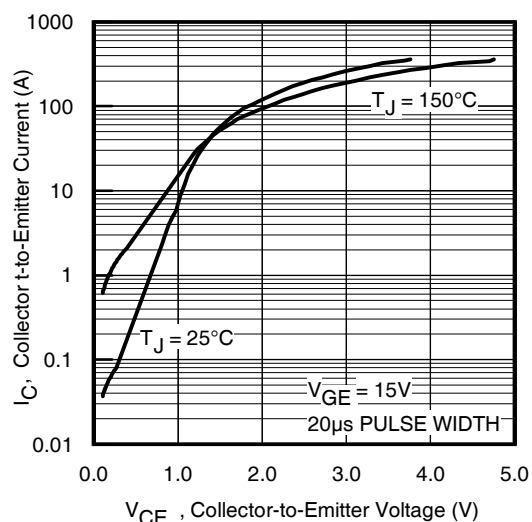


Fig. 2 - Typical Output Characteristics

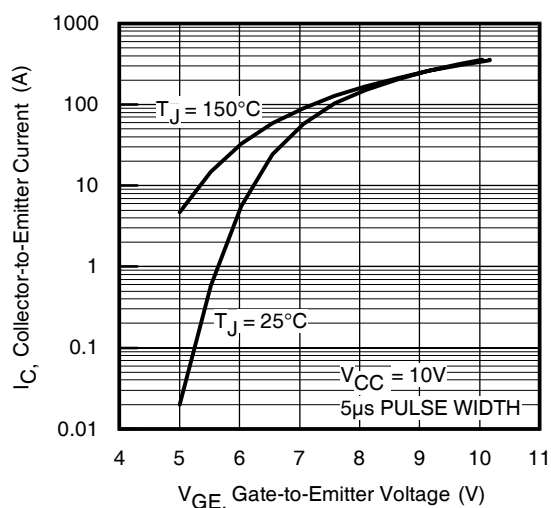


Fig. 3 - Typical Transfer Characteristics

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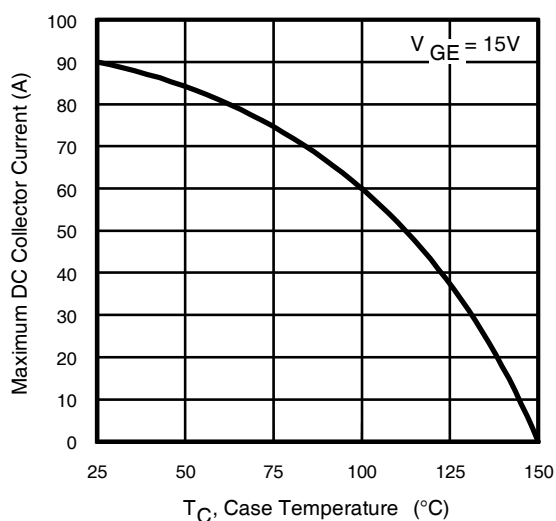


Fig. 4 - Maximum Collector Current vs. Case Temperature

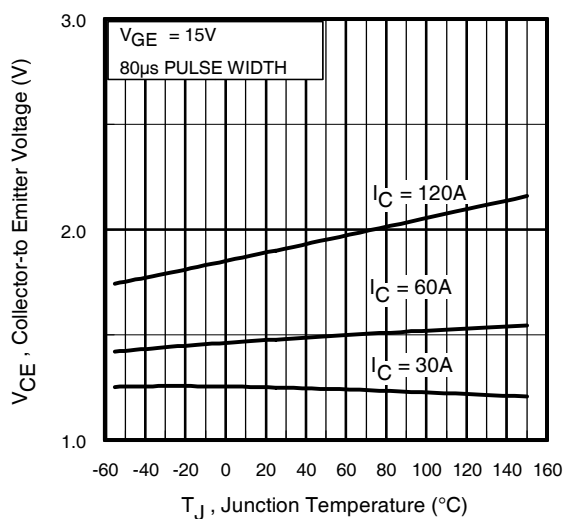


Fig. 5 - Typical Collector-to-Emitter Voltage vs. Junction Temperature

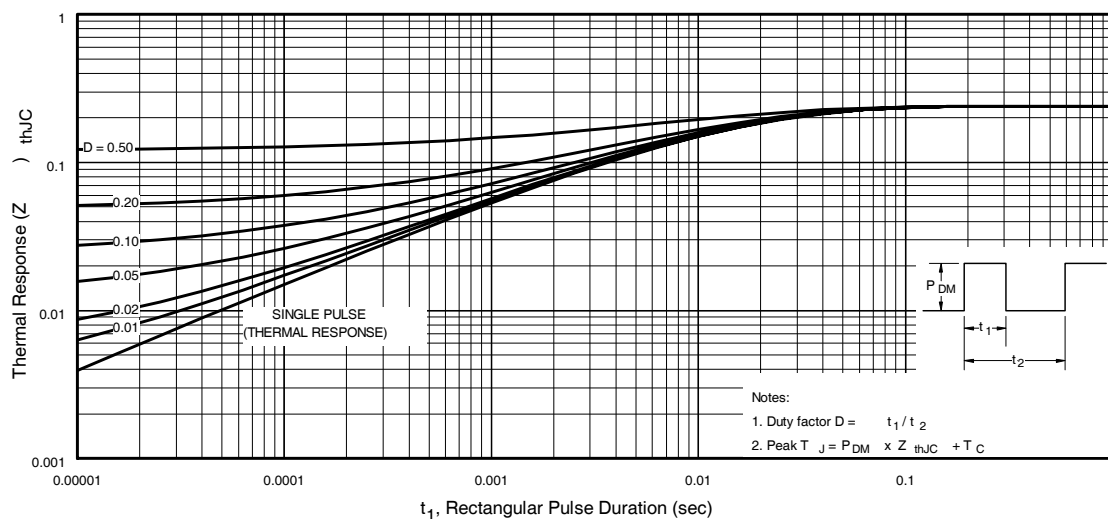


Fig. 6 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

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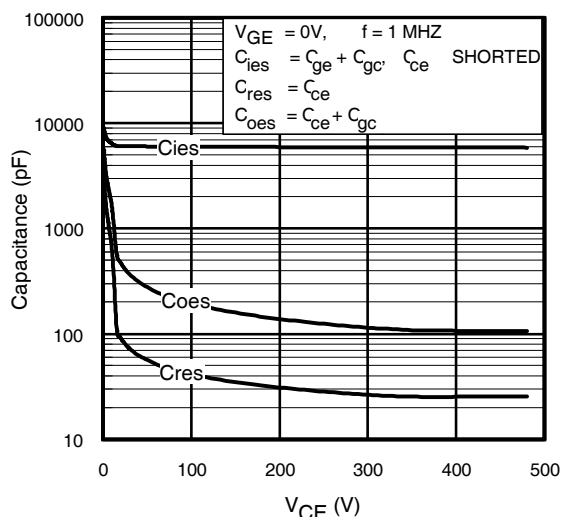


Fig. 7 - Typical Capacitance vs. Collector-to-Emitter Voltage

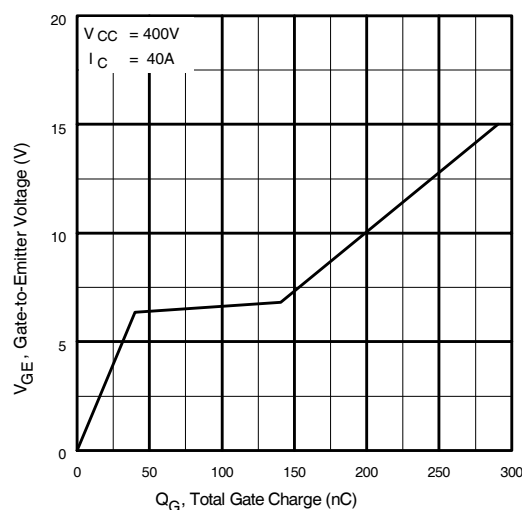


Fig. 8 - Typical Gate Charge vs. Gate-to-Emitter Voltage

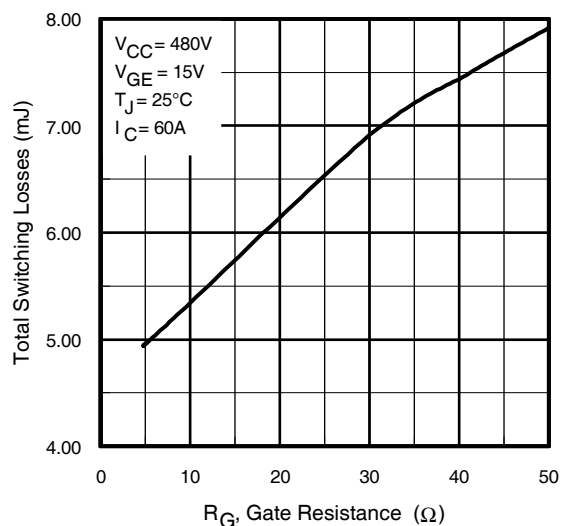


Fig. 9 - Typical Switching Losses vs. Gate Resistance

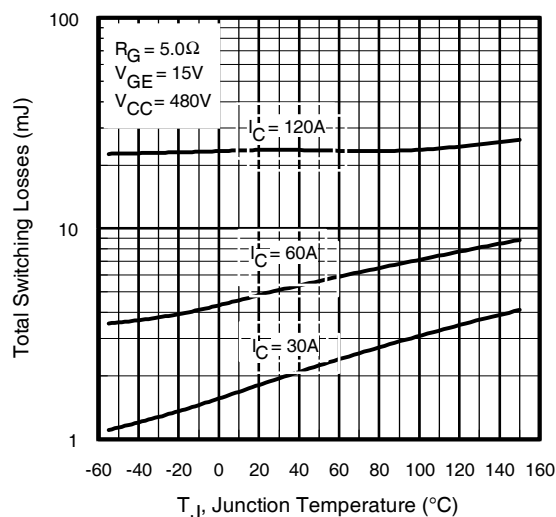


Fig. 10 - Typical Switching Losses vs. Junction Temperature

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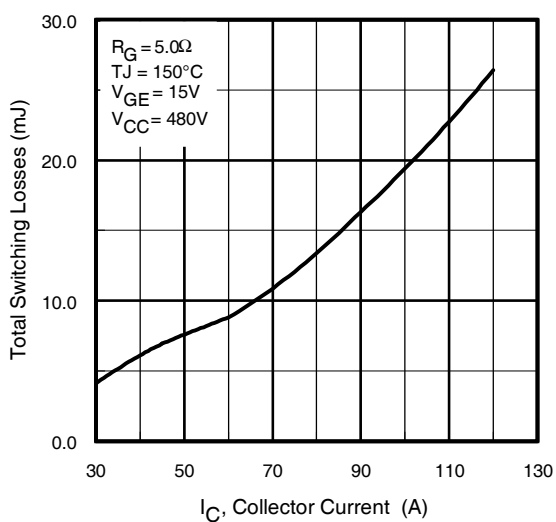


Fig. 11 - Typical Switching Losses vs. Collector-to-Emitter Current

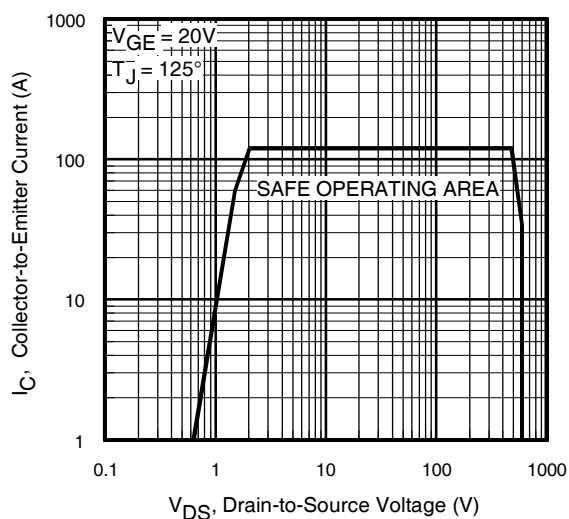


Fig. 12 - Turn-Off SOA

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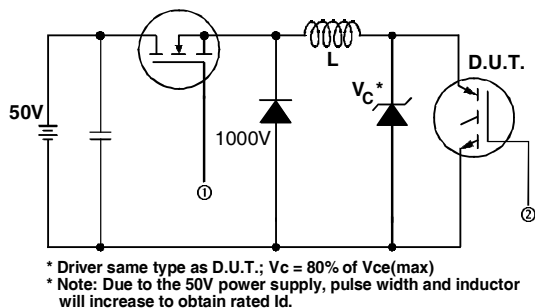


Fig. 13a - Clamped Inductive Load Test Circuit

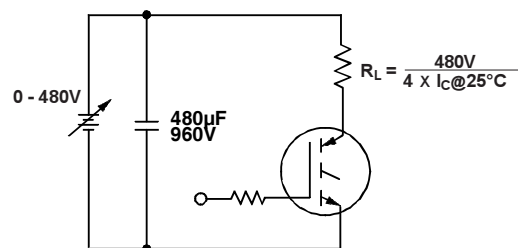


Fig. 13b - Pulsed Collector Current Test Circuit

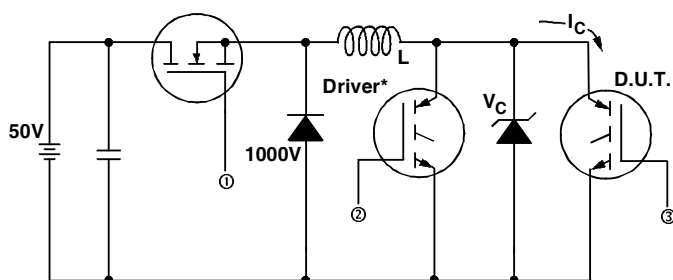


Fig. 14a - Switching Loss Test Circuit

* Driver same type as D.U.T., $V_c = 480V$

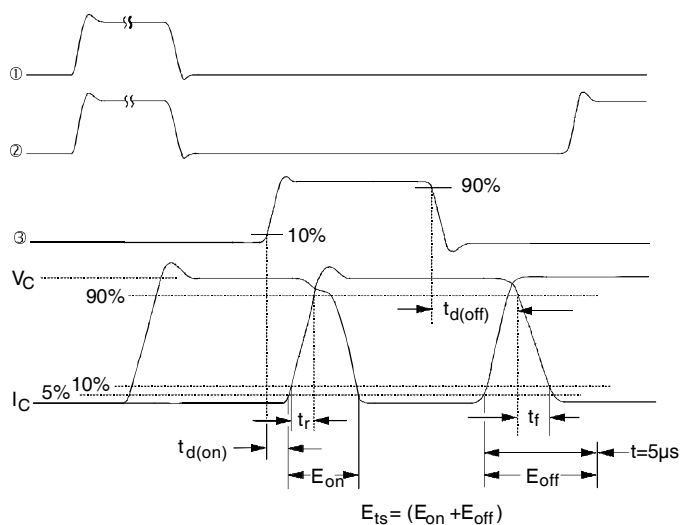


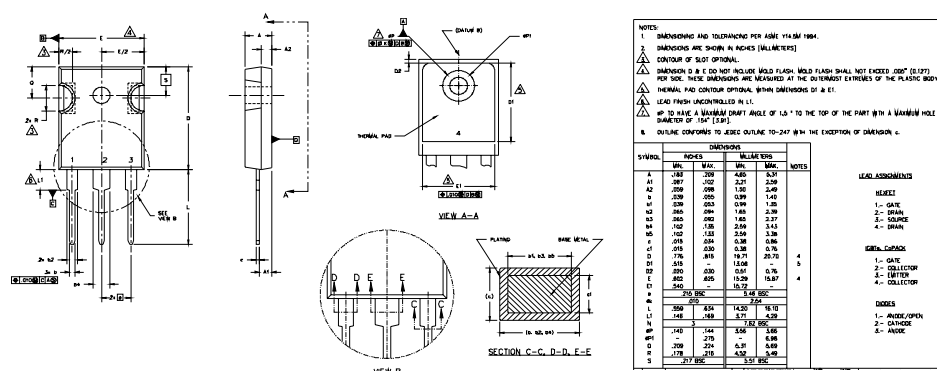
Fig. 14b - Switching Loss Waveforms

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TO-247AC Package Outline

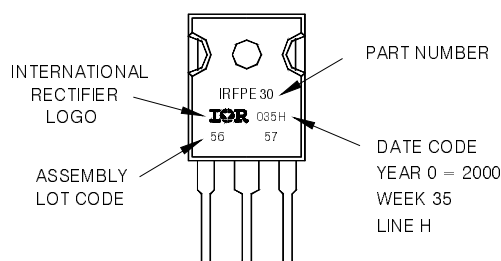
Dimensions are shown in millimeters (inches)



TO-247AC Part Marking Information

EXAMPLE: THIS IS AN IRFPE30
WITH ASSEMBLY
LOT CODE 5657
ASSEMBLED ON WW 35, 2000
IN THE ASSEMBLY LINE "H"

Note: "P" in assembly line position indicates "Lead-Free"



Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

Data and specifications subject to change without notice.
This product has been designed and qualified for the Industrial market.
Qualification Standards can be found on IR's Web site.

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